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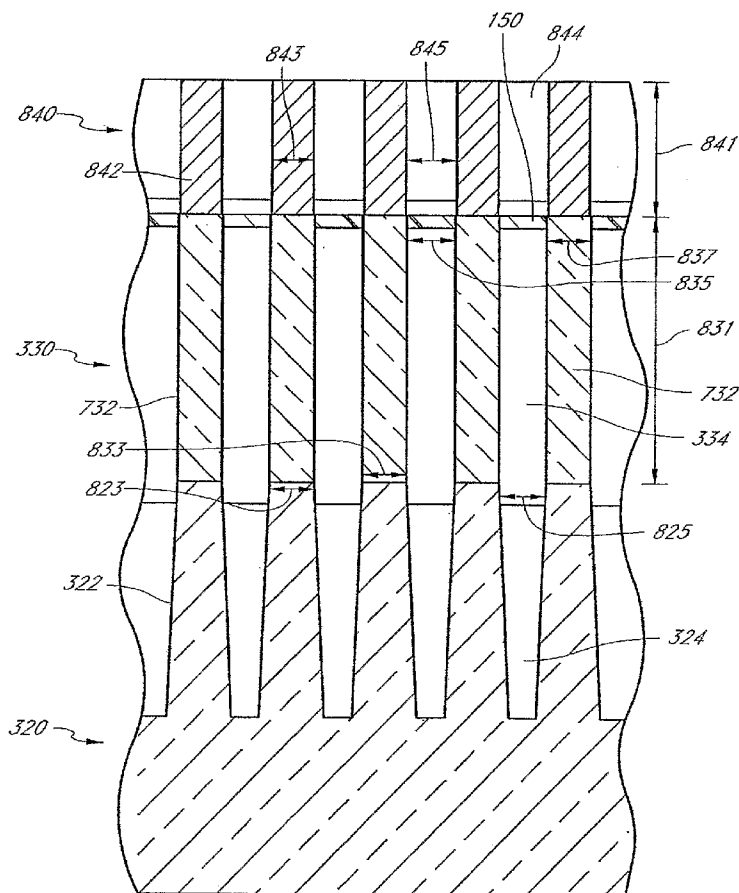
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(54) Title: METHOD OF FORMING PITCH MULTIPLIED CONTACTS



(57) Abstract: Methods of forming electrically conductive and/or semiconductive features for use in integrated circuits are disclosed. Various pattern transfer and etching steps can be used, in combination with pitch-reduction techniques, to create densely-packed features. The features can have a reduced pitch in one direction and a wider pitch in another direction. Conventional photo- lithography steps can be used in combination with pitch-reduction techniques to form elongate, pitch-reduced features such as bit-line contacts (732), for example.



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